



Data sheet acquired from Harris Semiconductor
SCHS168

November 1997

CD74HCT242, CD74HC243, CD74HCT243

High Speed CMOS Logic Quad-Bus Transceiver with Three-State Outputs

Features

- Typical Propagation Delay (A to B, B to A) of 7ns at $V_{CC} = 5V$, $C_L = 15pF$, $T_A = 25^\circ C$
- Three-State Outputs
- Buffered Inputs
- Fanout (Over Temperature Range)
 - Standard Outputs 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range . . . $-55^\circ C$ to $125^\circ C$
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: $N_{IL} = 30\%$, $N_{IH} = 30\%$ of V_{CC} at $V_{CC} = 5V$
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility, $V_{IL} = 0.8V$ (Max), $V_{IH} = 2V$ (Min)
 - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL} , V_{OH}

Description

The Harris CD74HCT242, CD74HC243 and CD74HCT243 silicon-gate CMOS three-state bidirectional inverting and non-inverting buffers are intended for two-way asynchronous communication between data buses. They have high drive current outputs which enable high-speed operation when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuits, and have speeds comparable to low power Schottky TTL circuits. They can drive 15 LSTTL loads.

The CD74HCT242 is an inverting buffer; the CD74HC243 and CD74HCT243 are non-inverting buffers.

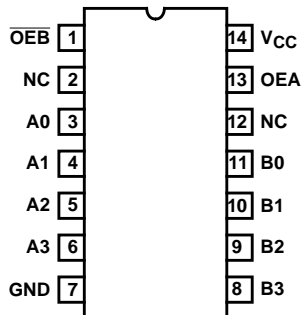
The states of the output enables (\overline{OEB} , OEA) determine both the direction of flow (A to B, B to A), and the three-state mode.

Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HC243E	-55 to 125	14 Ld PDIP	E14.3
CD74HC243M	-55 to 125	14 Ld SOIC	M14.15
CD74HCT243M	-55 to 125	14 Ld SOIC	M14.15

Pinout

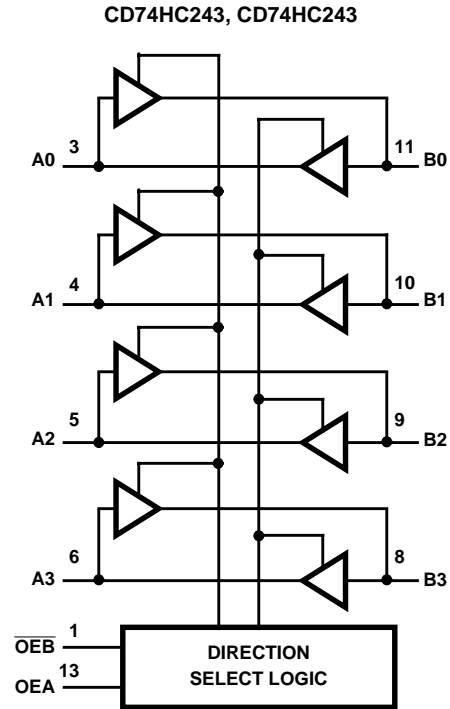
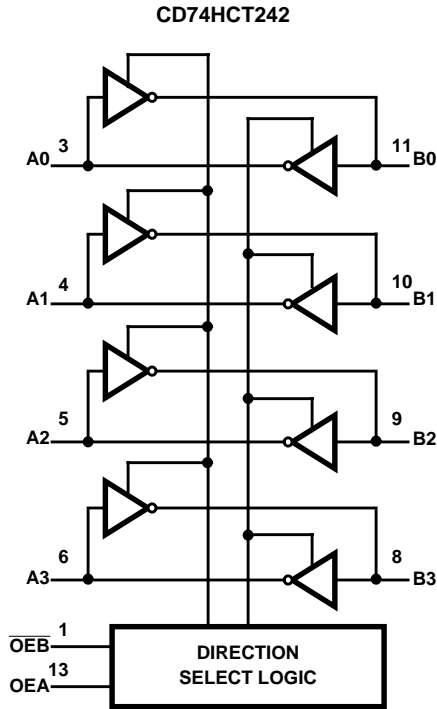
CD74HCT242, CD74HC243, CD74HCT243
(PDIP, SOIC)
TOP VIEW



NOTES:

1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
2. Wafer or die for this part number is available which meets all electrical specifications. Please contact your local sales

Functional Diagrams



TRUTH TABLE

CONTROL INPUTS		HCT242 SERIES		HC, HCT243 SERIES	
		DATA PORT STATUS		DATA PORT STATUS	
\overline{OEB}	OEA	An	Bn	An	Bn
H	H	\overline{O}	I	O	I
L	H	Z	Z	Z	Z
H	L	Z	Z	Z	Z
L	L	I	\overline{O}	I	O

NOTE:

H = High Voltage Level

L = Low Voltage Level

I = Input

O = Output (Same Level as Input)

\overline{O} = Output (Inversion of Input Level)

Z = High Impedance

To prevent excess currents in the High Z modes all I/O terminals should be terminated with 10kΩ to 1MΩ resistors.

Absolute Maximum Ratings

DC Supply Voltage, V_{CC} -0.5V to 7V
 DC Input Diode Current, I_{IK}
 For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$ $\pm 20mA$
 DC Output Diode Current, I_{OK}
 For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$ $\pm 20mA$
 DC Drain Current, per Output, I_O
 For $-0.5V < V_O < V_{CC} + 0.5V$ $\pm 35mA$
 DC Output Source or Sink Current per Output Pin, I_O
 For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$ $\pm 25mA$
 DC V_{CC} or Ground Current, I_{CC} $\pm 70mA$

Thermal Information

Thermal Resistance (Typical, Note 3) θ_{JA} ($^{\circ}C/W$)
 PDIP Package 90
 SOIC Package 175
 Maximum Junction Temperature $150^{\circ}C$
 Maximum Storage Temperature Range $-65^{\circ}C$ to $150^{\circ}C$
 Maximum Lead Temperature (Soldering 10s) $300^{\circ}C$
 (SOIC - Lead Tips Only)

Operating Conditions

Temperature Range (T_A) $-55^{\circ}C$ to $125^{\circ}C$
 Supply Voltage Range, V_{CC}
 HC Types 2V to 6V
 HCT Types 4.5V to 5.5V
 DC Input or Output Voltage, V_I, V_O 0V to V_{CC}
 Input Rise and Fall Time
 2V 1000ns (Max)
 4.5V 500ns (Max)
 6V 400ns (Max)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- 3. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25 $^{\circ}C$			-40 $^{\circ}C$ TO 85 $^{\circ}C$		-55 $^{\circ}C$ TO 125 $^{\circ}C$		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	6	5.9	-	-	5.9	-	5.9	-	V
			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	-7.8	6	5.48	-	-	5.34	-	5.2	-	V
			0.02	2	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads	V_{OL}	V_{IH} or V_{IL}	6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V _I (V)	I _O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Input Leakage Current	I _I	V _{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	I _{CC}	V _{CC} or GND	0	6	-	-	8	-	80	-	160	μA
Three-State Leakage Current	I _{OZ}	V _{IL} or V _{IH}	-	6	-	-	±0.5	-	±0.5	-	±10	μA
HCT TYPES												
High Level Input Voltage	V _{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V _{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I _I	V _{CC} to GND	0	5.5	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	I _{CC}	V _{CC} or GND	0	5.5	-	-	8	-	80	-	160	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 4)	ΔI _{CC}	V _{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA
Three-State Leakage Current	I _{OZ}	V _{IL} or V _{IH}	-	5.5	-	-	±0.5	-	±5.0	-	±10	μA

NOTE:

- 4. For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
An, Bn	1.1
OEA, \overline{OEB}	0.6

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., 360μA max at 25°C.

CD74HCT242, CD74HC243, CD74HCT243

Switching Specifications Input $t_r, t_f = 6\text{ns}$

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
HC TYPES								
Propagation Delay Data to Outputs (HC243)	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	2	-	90	115	135	ns
			4.5	-	18	23	27	ns
		$C_L = 15\text{pF}$	5	7	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	15	20	23	ns
Output High-Z, to High Level to Low Level	t_{PZL}, t_{PZH}	$C_L = 50\text{pF}$	2	-	150	190	225	ns
		$C_L = 50\text{pF}$	4.5	-	30	38	45	ns
		$C_L = 15\text{pF}$	5	12	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	26	33	38	ns
Output High Level, Output Low Level to High-Z	t_{PHZ}, t_{PLZ}	$C_L = 50\text{pF}$	2	-	150	190	225	ns
		$C_L = 50\text{pF}$	4.5	-	30	38	45	ns
		$C_L = 15\text{pF}$	5	12	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	26	33	38	ns
Output Transition Times	t_{TLH}, t_{THL}	$C_L = 50\text{pF}$	2	-	60	75	90	ns
			4.5	-	12	15	18	ns
			6	-	10	13	15	ns
Input Capacitance	C_I	-	-	-	10	10	10	pF
Three-State Output Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (HC243) (Notes 5, 6)	C_{PD}	-	5	80	-	-	-	pF
HCT TYPES								
Propagation Delay Data to Outputs (HCT242)	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	4.5	-	20	25	30	ns
		$C_L = 15\text{pF}$	5	8	-	-	-	ns
Propagation Delay Data to Outputs (HCT243)	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	4.5	-	22	28	33	ns
		$C_L = 15\text{pF}$	5	9	-	-	-	ns
Output High-Z to High Level to Low Level	t_{PZH}, t_{PZL}	$C_L = 50\text{pF}$	4.5	-	34	43	51	ns
		$C_L = 15\text{pF}$	5	14	-	-	-	ns
Output High Level, Output Low Level to High-Z	t_{PHZ}, t_{PLZ}	$C_L = 50\text{pF}$	4.5	-	35	44	53	ns
		$C_L = 15\text{pF}$	5	14	-	-	-	ns
Output Transition Times	t_{TLH}, t_{THL}	$C_L = 50\text{pF}$	4.5	-	12	15	18	ns
Input Capacitance	C_I	-	-	-	10	10	10	pF
Three-State Output Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 5, 6)	C_{PD}	HCT242	5	90	-	-	-	pF
		HCT243	5	91	-	-	-	pF

NOTES:

- C_{PD} is used to determine the dynamic power consumption, per channel.
- $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, f_O = Output Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms

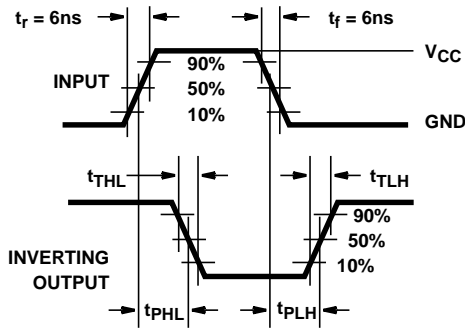


FIGURE 1. HC AND HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

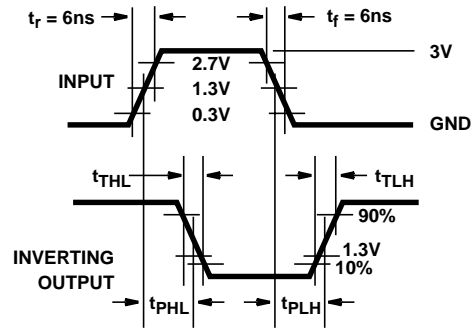


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

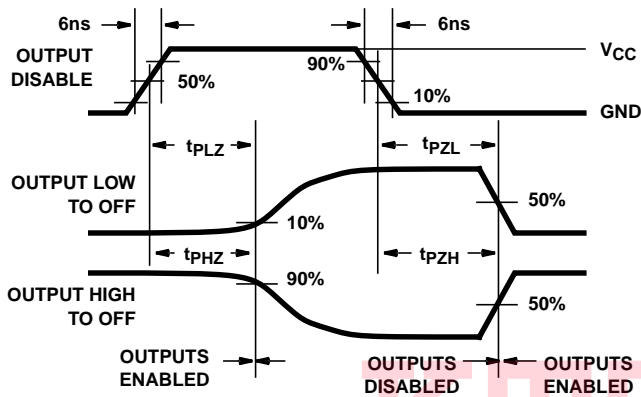


FIGURE 3. HC THREE-STATE PROPAGATION DELAY WAVEFORM

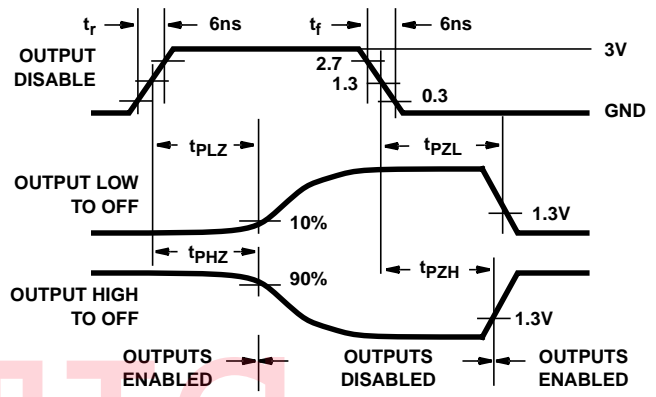
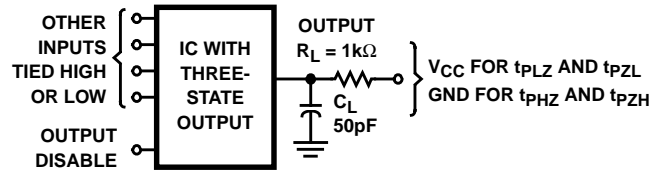


FIGURE 4. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output $R_L = 1k\Omega$ to V_{CC} , $C_L = 50pF$.

FIGURE 5. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

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